

# Table of Contents

<b>Metastability of Interstitial Clusters in Ion-Damaged Silicon Studied by Isothermal Capacitance Transient Spectroscopy</b> P.K. Giri	1
<b>Optimization of Off-Oriented Ge Substrates for MOVPE-Grown GaAs Solar Cells</b> M.K. Hudait and S.B. Krupanidhi	15
<b>On the Role of Bulk Recombination of Intrinsic Point Defects in Si and their Interaction with the Surface in the Course of {113} Defect Growth: a Kinetic Study by in situ HVEM Irradiation</b> L.I. Fedina	21
<b>Cavity Formation in Helium-Implanted Silicon - Temperature Dependence</b> J.F. Barbot, E. Oliviero, M. David, S. Rousselet, M.F. Beaufort and A. van Veen	37
<b>Shear Moduli of Silicon and Germanium in Semiconducting and Metallic Phases</b> L. Burakovsky and D.L. Preston	43
<b>Tracer Diffusion in the Concentrated Lattice Gas with Self-Excitation</b> I.V. Belova and G.E. Murch	55
<b>Defect Luminescence in Some Layered Binary Chalcogenide Semiconductors</b> A. Aydinli and N.M. Gasanly	61
<b>The Effect of Boron Concentration upon Defect Formation after Laser Thermal Processing using Molecular Dynamics</b> L. Wang, C.S. Murthy and P. Clancy	71
<b>Defect States in InAs Quantum Dots Characterized by Photo-Induced Current Transient Spectroscopy</b> H.Y. Cho	81
<b>Redistribution of Point Defects in the Crystalline Lattice of a Semiconductor in an Inhomogeneous Temperature Field</b> A. Medvid	89
<b>Monte Carlo Theoretical Study of Defect Generation at Heterovalent ZnSe/GaAs Epitaxial Interfaces</b> T. Nakayama	103
<b>A Simple Method for Determining the Basic Diffusion Parameters of Dopants using an Analytical Form of the Concentration Profile</b> E. Antoncik	113
<b>An Exact Formula for the Effective Diffusion Coefficient of Dopants in Semiconductors</b> E. Antoncik	123
<b>Abstracts</b>	1